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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	100
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 42x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk20dx256vlq10r

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3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

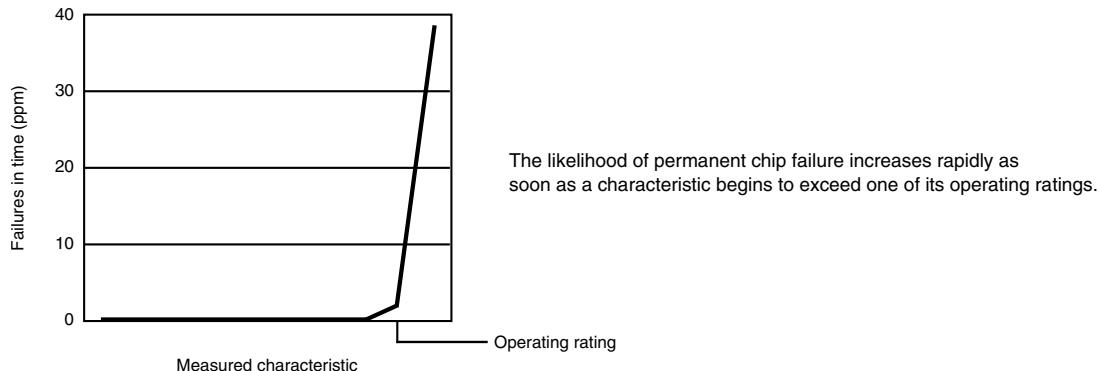
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.5 Result of exceeding a rating



5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage				
	• $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$0.7 \times V_{DD}$	—	V	
	• $1.7 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$	$0.75 \times V_{DD}$	—	V	
V_{IL}	Input low voltage				
	• $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	—	$0.35 \times V_{DD}$	V	
	• $1.7 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$	—	$0.3 \times V_{DD}$	V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICDIO}	Digital pin negative DC injection current — single pin	-5	—	mA	1
	• $V_{IN} < V_{SS}-0.3\text{V}$				
I_{ICAIO}	Analog ² , EXTAL, and XTAL pin DC injection current — single pin			mA	3
	• $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection)	-5	—		
	• $V_{IN} > V_{DD}+0.3\text{V}$ (Positive current injection)	—	+5		
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins			mA	
	• Negative current injection	-25	—		
	• Positive current injection	—	+25		
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	4
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All 5 V tolerant digital I/O pins are internally clamped to V_{SS} through an ESD protection diode. There is no diode connection to V_{DD} . If V_{IN} is less than V_{DIO_MIN} , a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO_MIN}-V_{IN})/I_{ICDIO}$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function. Additionally, EXTAL and XTAL are analog pins.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX} , a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/I_{ICAIO}$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/I_{ICAIO}$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.
4. Open drain outputs must be pulled to VDD.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V _{LVW1H}	Low-voltage warning thresholds — high range					1
	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V _{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V _{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V _{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
V _{LVW1L}	Low-voltage warning thresholds — low range					1
	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V _{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V _{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V _{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength					
	• $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OH} = -9\text{mA}$	$V_{DD} - 0.5$	—	—	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OH} = -3\text{mA}$	$V_{DD} - 0.5$	—	—	V	
	Output high voltage — low drive strength					
V_{OL}	• $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OL} = -2\text{mA}$	$V_{DD} - 0.5$	—	—	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OL} = -0.6\text{mA}$	$V_{DD} - 0.5$	—	—	V	
	I_{OHT}	Output high current total for all ports	—	—	100	mA
	Output low voltage — high drive strength					²
I_{OLT}	• $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OL} = 10\text{mA}$	—	—	0.5	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OL} = 5\text{mA}$	—	—	0.5	V	
	Output low voltage — low drive strength					
	• $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, $I_{OL} = 2\text{mA}$	—	—	0.5	V	
	• $1.71 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$, $I_{OL} = 1\text{mA}$	—	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	—	100	mA	
I_{INA}	Input leakage current, analog pins and digital pins configured as analog inputs					^{3, 4}
	• $V_{SS} \leq V_{IN} \leq V_{DD}$	—	0.002	0.5	μA	
	• All pins except EXTAL32, XTAL32, EXTAL, XTAL	—	0.004	1.5	μA	
	• EXTAL (PTA18) and XTAL (PTA19)	—	0.075	10	μA	
I_{IND}	Input leakage current, digital pins					^{4, 5}
	• $V_{SS} \leq V_{IN} \leq V_{IL}$	—	0.002	0.5	μA	
	• All digital pins	—	0.002	0.5	μA	
	• $V_{IN} = V_{DD}$	—	0.002	0.5	μA	
I_{IND}	• All digital pins except PTD7	—	0.004	1	μA	
	• PTD7	—	—	—	—	
	Input leakage current, digital pins					^{4, 5, 6}
	• $V_{IL} < V_{IN} < V_{DD}$	—	18	26	μA	
	• $V_{DD} = 3.6 \text{ V}$	—	12	49	μA	
	• $V_{DD} = 3.0 \text{ V}$	—	8	13	μA	
	• $V_{DD} = 2.5 \text{ V}$	—	3	6	μA	
	• $V_{DD} = 1.7 \text{ V}$	—	—	—	—	

Table continues on the next page...

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip. <ul style="list-style-type: none">• V_{DD} slew rate $\geq 5.7 \text{ kV/s}$• V_{DD} slew rate $< 5.7 \text{ kV/s}$	—	300 1.7 V / (V_{DD} slew rate)	μs	1
	• VLLS1 → RUN	—	130	μs	
	• VLLS2 → RUN	—	92	μs	
	• VLLS3 → RUN	—	92	μs	
	• LLS → RUN	—	5.9	μs	
	• VLPS → RUN	—	5.0	μs	
	• STOP → RUN	—	5.0	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash <ul style="list-style-type: none">• @ 1.8V• @ 3.0V	— —	37 38	63 64	mA mA	2
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash <ul style="list-style-type: none">• @ 1.8V• @ 3.0V<ul style="list-style-type: none">• @ 25°C• @ 125°C	— — —	46 47 58	77 63 79	mA mA mA	3, 4
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	20	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	9	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	1.12	—	mA	6

Table continues on the next page...

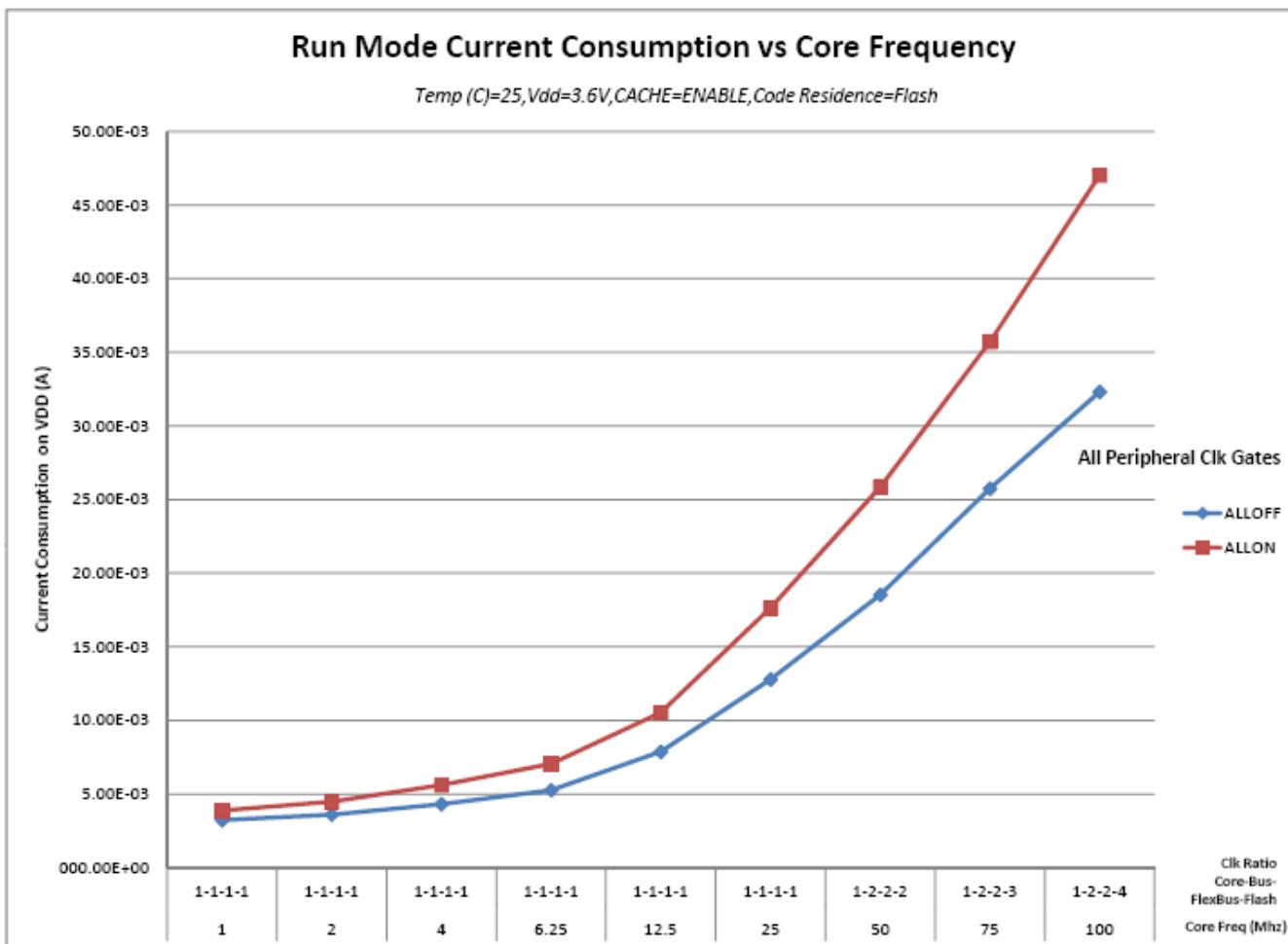


Figure 2. Run mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 144LQFP and 144MAPBGA

Symbol	Description	Frequency band (MHz)	144LQFP	144MAPBGA	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	23	12	dB μ V	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	27	24	dB μ V	
V _{RE3}	Radiated emissions voltage, band 3	150–500	28	27	dB μ V	
V _{RE4}	Radiated emissions voltage, band 4	500–1000	14	11	dB μ V	
V _{RE_IEC}	IEC level	0.15–1000	K	K	—	2, 3

- Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. $V_{DD} = 3.3$ V, $T_A = 25$ °C, $f_{OSC} = 12$ MHz (crystal), $f_{SYS} = 96$ MHz, $f_{BUS} = 48$ MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for “EMC design.”

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	100	MHz	
f_{SYS_USB}	System and core clock when Full Speed USB in operation	20	—	MHz	
f_{BUS}	Bus clock	—	50	MHz	
FB_CLK	FlexBus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode ¹					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
FB_CLK	FlexBus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	

Table continues on the next page...

6.3.1 MCG specifications

Table 15. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta f_{dco_res_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	% f_{dco}	1
$\Delta f_{dco_res_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM only	—	± 0.2	± 0.5	% f_{dco}	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature	—	+0.5/-0.7	± 3	% f_{dco}	1,
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C	—	± 0.3	± 3	% f_{dco}	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C	—	4	—	MHz	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C	3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00	(3/5) × f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11	(16/5) × f_{ints_t}	—	—	kHz	
FLL						
f_{fill_ref}	FLL reference frequency range	31.25	—	39.0625	kHz	
f_{dco}	DCO output frequency range	Low range (DRS=00) 640 × f_{fill_ref}	20	20.97	25	MHz
		Mid range (DRS=01) 1280 × f_{fill_ref}	40	41.94	50	MHz
		Mid-high range (DRS=10) 1920 × f_{fill_ref}	60	62.91	75	MHz
		High range (DRS=11) 2560 × f_{fill_ref}	80	83.89	100	MHz
$f_{dco_t_DMX32}$	DCO output frequency	Low range (DRS=00) 732 × f_{fill_ref}	—	23.99	—	MHz
		Mid range (DRS=01) 1464 × f_{fill_ref}	—	47.97	—	MHz
		Mid-high range (DRS=10) 2197 × f_{fill_ref}	—	71.99	—	MHz
		High range (DRS=11) 2929 × f_{fill_ref}	—	95.98	—	MHz

Table continues on the next page...

Table 16. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{pp}^5	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. $V_{DD}=3.3$ V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x, C_y can be provided by using either the integrated capacitors or by using external components.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.2.2 Oscillator frequency specifications

Table 17. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc_hi_1}$	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc_hi_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.

4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.3.3 32 kHz oscillator electrical characteristics

This section describes the module electrical characteristics.

6.3.3.1 32 kHz oscillator DC electrical specifications

Table 18. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{BAT}	Supply voltage	1.71	—	3.6	V
R_F	Internal feedback resistor	—	100	—	MΩ
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp} ¹	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.3.2 32 kHz oscillator frequency specifications

Table 19. 32 kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{ec_extal32}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$V_{ec_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
 2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
 3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT} .

6.4 Memories and memory interfaces

Table 28. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹ .	Min.	Typ. ²	Max.	Unit	Notes
f_{ADACK}	ADC asynchronous clock source	<ul style="list-style-type: none"> ADLPC = 1, ADHSC = 0 ADLPC = 1, ADHSC = 1 ADLPC = 0, ADHSC = 0 ADLPC = 0, ADHSC = 1 	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	<ul style="list-style-type: none"> 12-bit modes <12-bit modes 	— —	± 4 ± 1.4	± 6.8 ± 2.1	LSB ⁴	5
DNL	Differential non-linearity	<ul style="list-style-type: none"> 12-bit modes <12-bit modes 	— —	± 0.7 ± 0.2	-1.1 to +1.9 -0.3 to 0.5	LSB ⁴	5
INL	Integral non-linearity	<ul style="list-style-type: none"> 12-bit modes <12-bit modes 	— —	± 1.0 ± 0.5	-2.7 to +1.9 -0.7 to +0.5	LSB ⁴	5
E_{FS}	Full-scale error	<ul style="list-style-type: none"> 12-bit modes <12-bit modes 	— —	-4 -1.4	-5.4 -1.8	LSB ⁴	$V_{ADIN} = V_{DDA}$ 5
E_Q	Quantization error	<ul style="list-style-type: none"> 16-bit modes ≤ 13-bit modes 	— —	-1 to 0 —	— ± 0.5	LSB ⁴	
ENOB	Effective number of bits	16-bit differential mode <ul style="list-style-type: none"> Avg = 32 Avg = 4 16-bit single-ended mode <ul style="list-style-type: none"> Avg = 32 Avg = 4 	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	$6.02 \times ENOB + 1.76$			dB	
THD	Total harmonic distortion	16-bit differential mode <ul style="list-style-type: none"> Avg = 32 16-bit single-ended mode <ul style="list-style-type: none"> Avg = 32 	— —	-94 -85	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode <ul style="list-style-type: none"> Avg = 32 16-bit single-ended mode <ul style="list-style-type: none"> Avg = 32 	82 78	95 90	— —	dB dB	7

Table continues on the next page...

Table 30. 16-bit ADC with PGA characteristics (continued)

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
SFDR	Spurious free dynamic range	<ul style="list-style-type: none"> Gain=1 Gain=64 	85 53	105 88	— —	dB dB	16-bit differential mode, Average=32, f _{in} =100Hz
ENOB	Effective number of bits	• Gain=1, Average=4	11.6	13.4	—	bits	16-bit differential mode, f _{in} =100Hz
		• Gain=1, Average=8	8.0	13.6	—	bits	
		• Gain=64, Average=4	7.2	9.6	—	bits	
		• Gain=64, Average=8	6.3	9.6	—	bits	
		• Gain=1, Average=32	12.8	14.5	—	bits	
		• Gain=2, Average=32	11.0	14.3	—	bits	
		• Gain=4, Average=32	7.9	13.8	—	bits	
		• Gain=8, Average=32	7.3	13.1	—	bits	
		• Gain=16, Average=32	6.8	12.5	—	bits	
		• Gain=32, Average=32	6.8	11.5	—	bits	
		• Gain=64, Average=32	7.5	10.6	—	bits	
SINAD	Signal-to-noise plus distortion ratio	See ENOB	6.02 × ENOB + 1.76			dB	

1. Typical values assume V_{DDA} =3.0V, Temp=25°C, f_{ADCK}=6MHz unless otherwise stated.
2. This current is a PGA module adder, in addition to ADC conversion currents.
3. Between IN+ and IN-. The PGA draws a DC current from the input terminals. The magnitude of the DC current is a strong function of input common mode voltage (V_{CM}) and the PGA gain.
4. Gain = 2^{PGAG}
5. After changing the PGA gain setting, a minimum of 2 ADC+PGA conversions should be ignored.
6. Limit the input signal swing so that the PGA does not saturate during operation. Input signal swing is dependent on the PGA reference voltage and gain setting.

6.6.2 CMP and 6-bit DAC electrical specifications

Table 31. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V _{DD}	Supply voltage	1.71	—	3.6	V
I _{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I _{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V _{AIN}	Analog input voltage	V _{SS} – 0.3	—	V _{DD}	V
V _{AIO}	Analog input offset voltage	—	—	20	mV

Table continues on the next page...

Table 31. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
V_H	Analog comparator hysteresis ¹ <ul style="list-style-type: none"> • CR0[HYSTCTR] = 00 • CR0[HYSTCTR] = 01 • CR0[HYSTCTR] = 10 • CR0[HYSTCTR] = 11 	—	5	—	mV
V_{CMPOh}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD} -0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}/64$

6.8.9 SDHC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

Table 45. SDHC switching specifications

Num	Symbol	Description	Min.	Max.	Unit
		Operating voltage	1.71	3.6	V
Card input clock					
SD1	f _{pp}	Clock frequency (low speed)	0	400	kHz
	f _{pp}	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	f _{pp}	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f _{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t _{WL}	Clock low time	7	—	ns
SD3	t _{WH}	Clock high time	7	—	ns
SD4	t _{TLH}	Clock rise time	—	3	ns
SD5	t _{THL}	Clock fall time	—	3	ns
SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD6	t _{OD}	SDHC output delay (output valid)	-5	8.3	ns
SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)					
SD7	t _{ISU}	SDHC input setup time	5	—	ns
SD8	t _{IH}	SDHC input hold time	0	—	ns

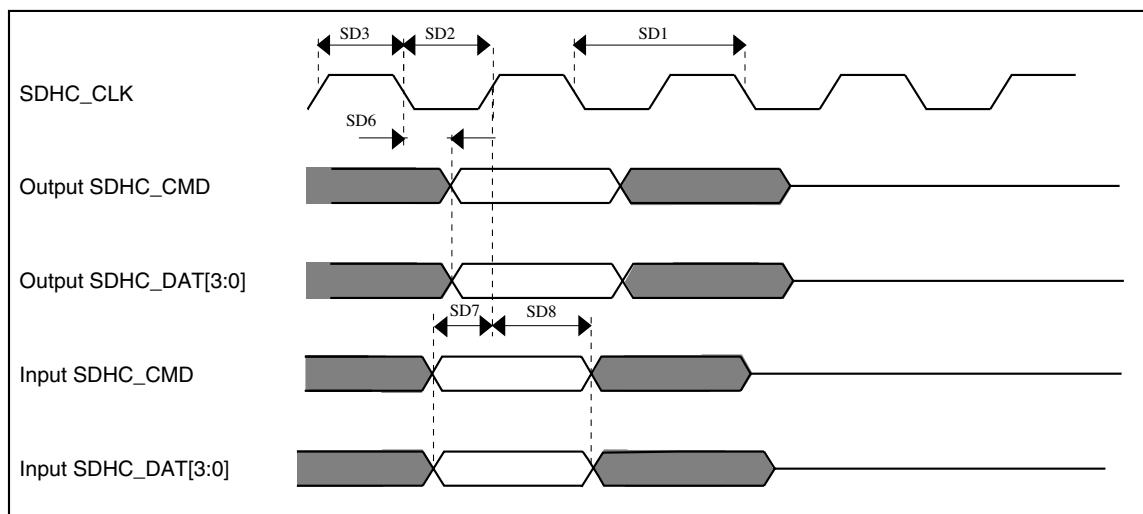


Figure 25. SDHC timing

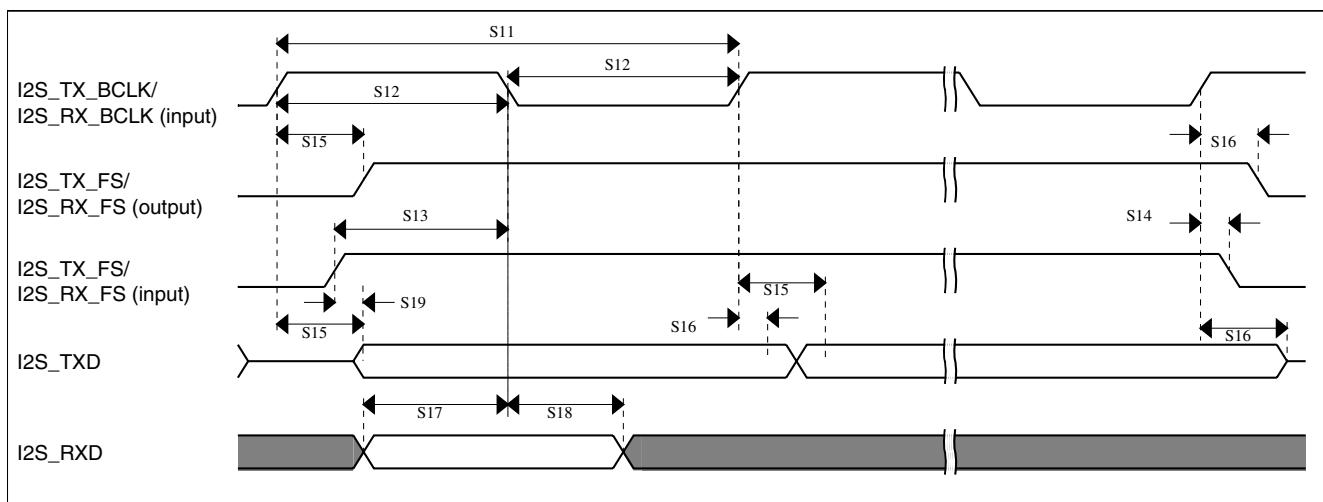


Figure 27. I2S/SAI timing — slave modes

6.8.10.2 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 48. I2S/SAI master mode timing in Normal Run, Wait and Stop modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/I2S_RX_FS output invalid	-1.0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	20.5	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

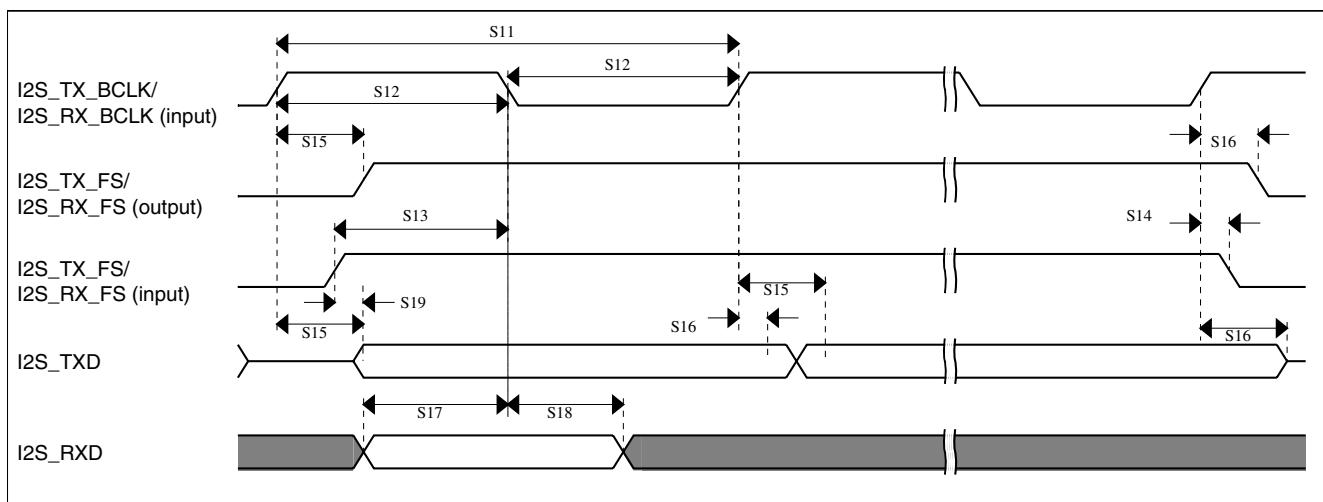


Figure 29. I2S/SAI timing — slave modes

6.8.10.3 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 50. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/I2S_RX_FS output valid	—	45	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

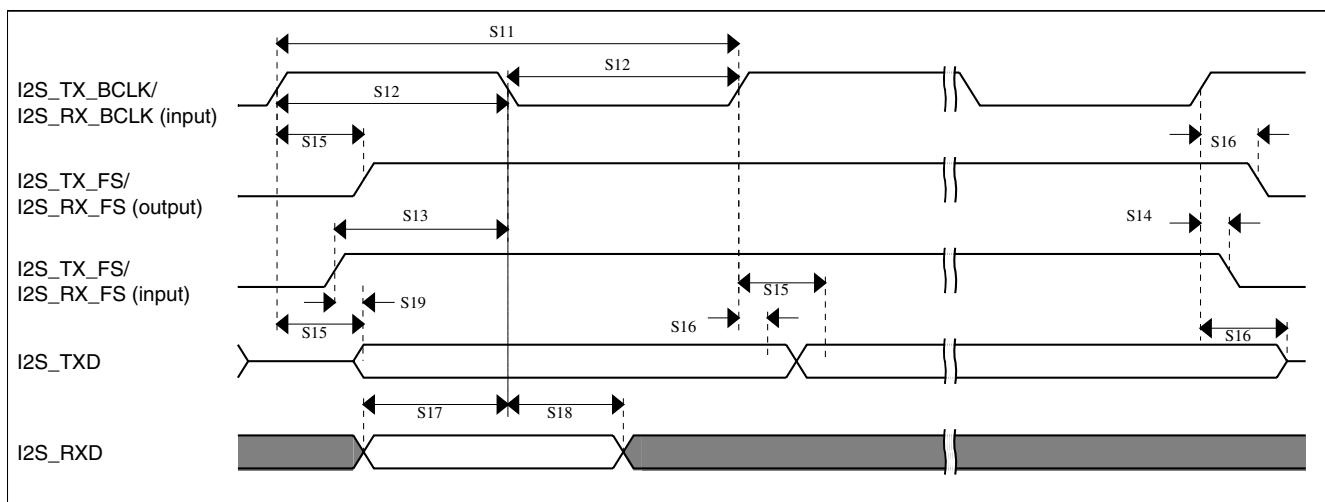


Figure 31. I2S/SAI timing — slave modes

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 52. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	8	15	MHz	2, 3
f_{ELEmax}	Electrode oscillator frequency	—	1	1.8	MHz	2, 4
C_{REF}	Internal reference capacitor	—	1	—	pF	
V_{DELTA}	Oscillator delta voltage	—	500	—	mV	2, 5
I_{REF}	Reference oscillator current source base current • 2 μ A setting (REFCHRG = 0) • 32 μ A setting (REFCHRG = 15)	—	2	3	μ A	2, 6
I_{ELE}	Electrode oscillator current source base current • 2 μ A setting (EXTCHRG = 0) • 32 μ A setting (EXTCHRG = 15)	—	36	50	μ A	2, 7
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	10
MaxSens	Maximum sensitivity	0.008	1.46	—	fF/count	11
Res	Resolution	—	—	16	bits	
T_{Con20}	Response time @ 20 pF	8	15	25	μ s	12
I_{TSI_RUN}	Current added in run mode	—	55	—	μ A	
I_{TSI_LP}	Low power mode current adder	—	1.3	2.5	μ A	13

8.1 K20 signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
—	L5	RTC_WAKEUP_B	RTC_WAKEUP_B	RTC_WAKEUP_B								
—	M5	NC	NC	NC								
—	A10	NC	NC	NC								
—	B10	NC	NC	NC								
—	C10	NC	NC	NC								
1	D3	PTE0	ADC1_SE4a	ADC1_SE4a	PTE0	SPI1_PCS1	UART1_TX	SDHC0_D1		I2C1_SDA	RTC_CLKOUT	
2	D2	PTE1/LLWU_P0	ADC1_SE5a	ADC1_SE5a	PTE1/LLWU_P0	SPI1_SOUT	UART1_RX	SDHC0_D0		I2C1_SCL	SPI1_SIN	
3	D1	PTE2/LLWU_P1	ADC1_SE6a	ADC1_SE6a	PTE2/LLWU_P1	SPI1_SCK	UART1_CTS_b	SDHC0_DCLK				
4	E4	PTE3	ADC1_SE7a	ADC1_SE7a	PTE3	SPI1_SIN	UART1_RTS_b	SDHC0_CMD			SPI1_SOUT	
5	E5	VDD	VDD	VDD								
6	F6	VSS	VSS	VSS								
7	E3	PTE4/LLWU_P2	DISABLED		PTE4/LLWU_P2	SPI1_PCS0	UART3_TX	SDHC0_D3				
8	E2	PTE5	DISABLED		PTE5	SPI1_PCS2	UART3_RX	SDHC0_D2				
9	E1	PTE6	DISABLED		PTE6	SPI1_PCS3	UART3_CTS_b	I2S0_MCLK			USB_SOF_OUT	
10	F4	PTE7	DISABLED		PTE7		UART3_RTS_b	I2S0_RXD0				
11	F3	PTE8	DISABLED		PTE8	I2S0_RXD1	UART5_TX	I2S0_RX_FS				
12	F2	PTE9	DISABLED		PTE9	I2S0_TXD1	UART5_RX	I2S0_RX_BCLK				
13	F1	PTE10	DISABLED		PTE10		UART5_CTS_b	I2S0_RXD0				
14	G4	PTE11	DISABLED		PTE11		UART5_RTS_b	I2S0_TX_FS				
15	G3	PTE12	DISABLED		PTE12			I2S0_TX_BCLK				
16	E6	VDD	VDD	VDD								
17	F7	VSS	VSS	VSS								
18	H3	VSS	VSS	VSS								
19	H1	USB0_DP	USB0_DP	USB0_DP								
20	H2	USB0_DM	USB0_DM	USB0_DM								
21	G1	VOUT33	VOUT33	VOUT33								
22	G2	VREGIN	VREGIN	VREGIN								

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
103	B12	PTC0	ADC0_SE14/ TSI0_CH13	ADC0_SE14/ TSI0_CH13	PTC0	SPI0_PCS4	PDB0_EXTRG		FB_AD14	I2S0_TXD1		
104	B11	PTC1/ LLWU_P6	ADC0_SE15/ TSI0_CH14	ADC0_SE15/ TSI0_CH14	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_b	FTM0_CH0	FB_AD13	I2S0_RXD0		
105	A12	PTC2	ADC0_SE4b/ CMP1_IN0/ TSI0_CH15	ADC0_SE4b/ CMP1_IN0/ TSI0_CH15	PTC2	SPI0_PCS2	UART1_CTS_b	FTM0_CH1	FB_AD12	I2S0_TX_FS		
106	A11	PTC3/ LLWU_P7	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT	I2S0_TX_BCLK		
107	H8	VSS	VSS	VSS								
108	—	VDD	VDD	VDD								
109	A9	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3	FB_AD11	CMP1_OUT		
110	D8	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0	FB_AD10	CMP0_OUT		
111	C8	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_EXTRG	I2S0_RX_BCLK	FB_AD9	I2S0_MCLK		
112	B8	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN	USB_SOF_OUT	I2S0_RX_FS	FB_AD8			
113	A8	PTC8	ADC1_SE4b/ CMP0_IN2	ADC1_SE4b/ CMP0_IN2	PTC8			I2S0_MCLK	FB_AD7			
114	D7	PTC9	ADC1_SE5b/ CMP0_IN3	ADC1_SE5b/ CMP0_IN3	PTC9			I2S0_RX_BCLK	FB_AD6	FTM2_FLT0		
115	C7	PTC10	ADC1_SE6b	ADC1_SE6b	PTC10	I2C1_SCL		I2S0_RX_FS	FB_AD5			
116	B7	PTC11/ LLWU_P11	ADC1_SE7b	ADC1_SE7b	PTC11/ LLWU_P11	I2C1_SDA		I2S0_RXD1	FB_RW_b			
117	A7	PTC12	DISABLED		PTC12		UART4_RTS_b		FB_AD27			
118	D6	PTC13	DISABLED		PTC13		UART4_CTS_b		FB_AD26			
119	C6	PTC14	DISABLED		PTC14		UART4_RX		FB_AD25			
120	B6	PTC15	DISABLED		PTC15		UART4_TX		FB_AD24			
121	—	VSS	VSS	VSS								
122	—	VDD	VDD	VDD								
123	A6	PTC16	DISABLED		PTC16	CAN1_RX	UART3_RX		FB_CS5_b/ FB_TSI21/ FB_BE23_16_b			
124	D5	PTC17	DISABLED		PTC17	CAN1_TX	UART3_TX		FB_CS4_b/ FB_TSI20/ FB_BE31_24_b			
125	C5	PTC18	DISABLED		PTC18		UART3_RTS_b		FB_TBST_b/ FB_CS2_b/ FB_BE15_8_b			
126	B5	PTC19	DISABLED		PTC19		UART3_CTS_b		FB_CS3_b/ FB_BE7_0_b	FB_TA_b		